



Pin Definition:

- 1. Base 2. Collector
- 3. Emitter

PRODUCT SUMMARY

BV _{CEO}	400V
BV _{CBO}	700V
Ι _C	2A
V _{CE(SAT)}	1.1V @ I _C =1A, I _B =0.25A

Features

- Build-in Free-wheeling Diode Makes Efficient Anti-saturation • Operation
- No Need to Interest h_{FE} Value Because of Low Variable • Storage-time Spread Even Though Comer Spirit Product.
- Low Base Drive Requirement •
- Suitable for Half Bridge Light Ballast Application •

Structure

- Silicon Triple Diffused Type •
- NPN Silicon Transistor with Diode .

Ordering Information

Part No.	Package	Packing
TSC5302DCP ROG	TO-252	2.5kpcs / 13" Reel
TSC5302DCH C5G	TO-251	75pcs / Tube

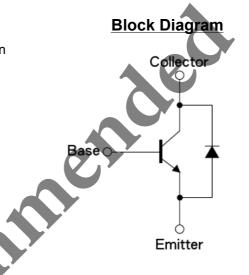
Note: "G" denote for Halogen Free Product

Absolute Maximum Ratings (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Collector-Base Voltage		V _{CBO}	700	V	
Collector-Emitter Voltage		V _{CEO}	400	V	
Emitter-Base Voltage		V _{EBO}	10	V	
Collector Current		Ι _C	2	А	
Collector Peak Current (tp <5ms)		I _{CM}	4	А	
Base Current		Ι _Β	1	А	
Base Peak Current (tp <5ms)		I _{BM}	2	А	
Tatal Dissipation @ Ta < 05%	TO-251	D	1.5	14/	
Total Dissipation @ $Tc \le 25^{\circ}C$	TO-252	P _{tot}	25	W	
Maximum Operating Junction Temperature		TJ	+150	°C	
Storage Temperature Range		T _{STG}	-65 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Case Thermal Resistance	Rθ _{JC}	6.25	°C/W
Junction to Ambient Thermal Resistance	RƏ _{JA}	100	°C/W





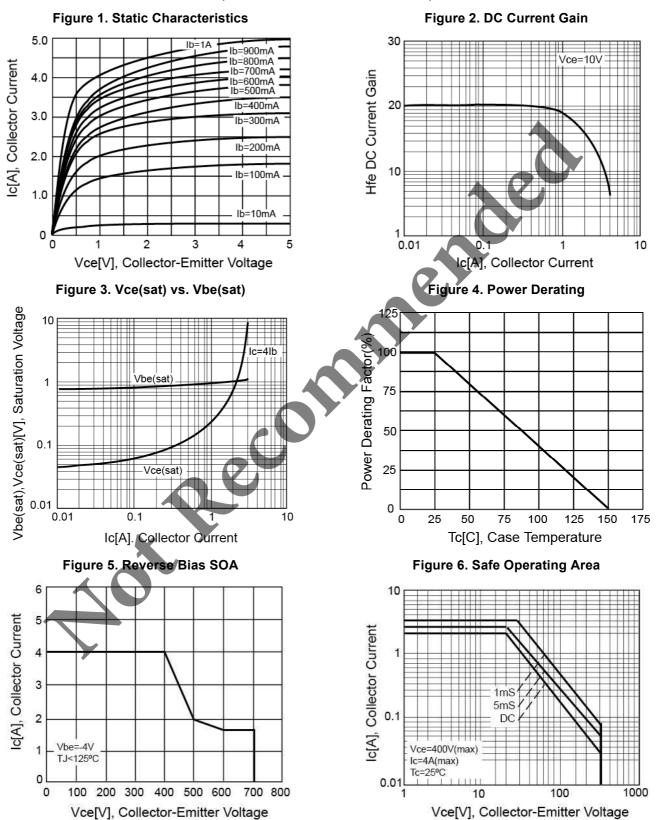
Electrical Specifications (Ta = 25°C unless otherwise noted)

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Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Collector-Base Voltage	$I_{\rm C} = 1 {\rm mA}, I_{\rm B} = 0$	BV_{CBO}	700			V
Collector-Emitter Breakdown Voltage ^a	I _C = 10mA, I _E = 0	BV_{CEO}	400			V
Emitter-Base Breakdown Voltage	I _E = 1mA, I _C = 0	BV_{EBO}	10			V
Collector Cutoff Current	V _{CB} = 700V, I _E = 0	I _{CBO}			1	μA
Emitter Cutoff Current	$V_{EB} = 9V, I_{C} = 0$	I _{EBO}			1	μA
Collector-Emitter Saturation Voltage ^a	I _C =0.5A, I _B =0.1A	V _{CE(SAT)1}		(0.5	
	I _C =1A, I _B =0.25A	V _{CE(SAT)2}		1.1	1.5	V
Base-Emitter Saturation Voltage ^a	I _C =0.5A, I _B =0.1A	V _{BE(SAT)1}			1.1	
	I _C =1A, I _B =0.25A	V _{BE(SAT)2}			1.2	V
DC Current Gain	V _{CE} =5V, I _C =10mA	h _{FE} 1	10			
	V _{CE} =5V, I _C =400mA	h _{FE} 2	10		30	
	V _{CE} =5V, I _C =1A	h _{FE} 3	5			
Turn On Time	V _{CC} =250V, I _C =1A,	ton		0.15	0.3	μs
Storage Time	I _{B1} =I _{B2} =0.2A, t _p =25μs	tstg		0.5	0.9	μs
Fall Time	Duty Cycle<1%	t _f		0.2	0.4	μs
Diode						
Fall Time	I _C =1A	t⊧			800	μs
Forward Voltage Drop	I _C =1A	Vf			1.4	V

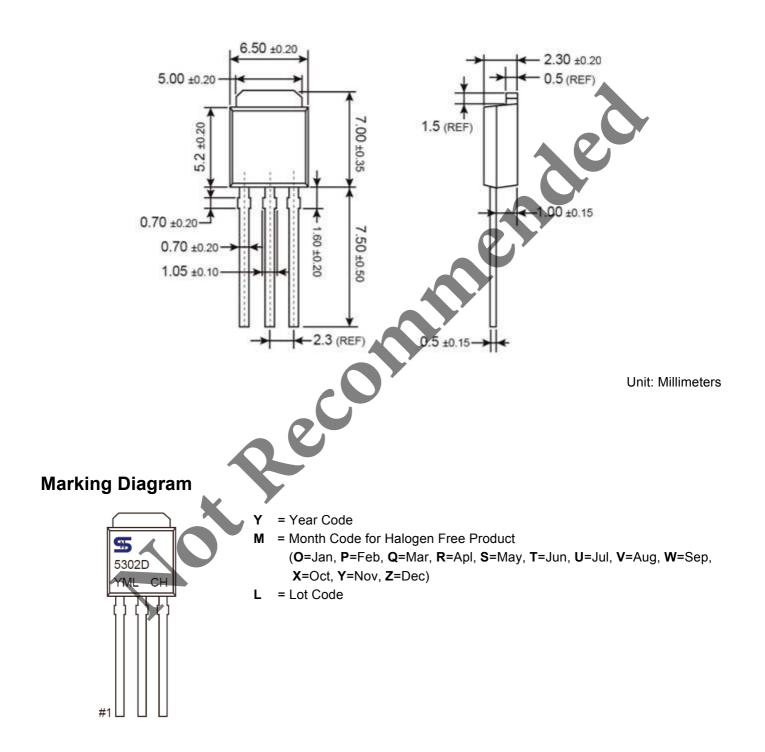


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)



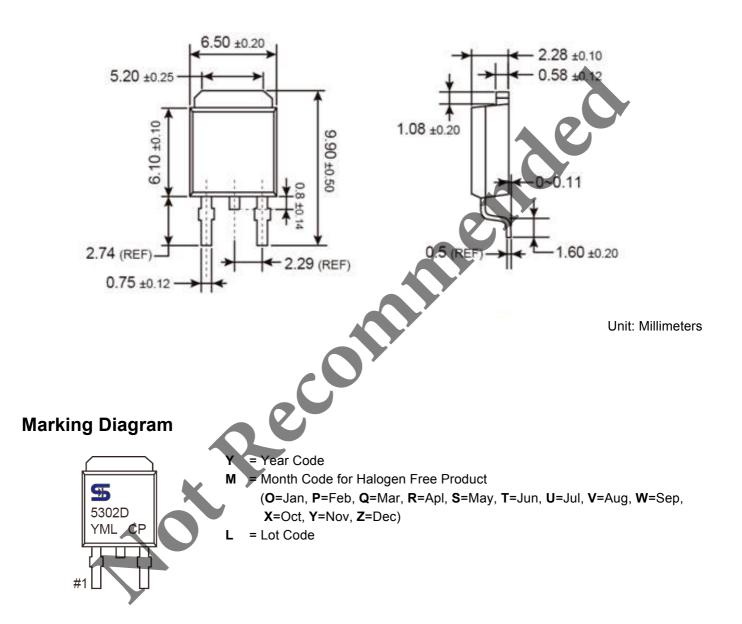


TO-251 Mechanical Drawing





TO-252 Mechanical Drawing







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